Clock	Clear	Load	Increment	Operation
$\uparrow$	0	0	0	No change
1	0	0	1	Increment count by 1
$\uparrow$	0	1	×	Load inputs $I_0$ through $I_3$
$\uparrow$	1	×	×	Clear outputs to 0

**TABLE 2-5** Function Table for the Register of Fig. 2-12

increment

operations. The *increment* operation adds one to the content of a register. By enabling the count input during one clock period, the content of the register can be incremented by one.

# 2-7 Memory Unit

word

byte

A memory unit is a collection of storage cells together with associated circuits needed to transfer information in and out of storage. The memory stores binary information in groups of bits called *words*. A word in memory is an entity of bits that move in and out of storage as a unit. A memory word is a group of l's and 0's and may represent a number, an instruction code, one or more alphanumeric characters, or any other binary-coded information. A group of eight bits is called a *byte*. Most computer memories use words whose number of bits is a multiple of 8. Thus a 16-bit word contains two bytes, and a 32-bit word is made up of four bytes. The capacity of memories in commercial computers is usually stated as the total number of bytes that can be stored.

The internal structure of a memory unit is specified by the number of words it contains and the number of bits in each word. Special input lines called address lines select one particular word. Each word in memory is assigned an identification number, called an address, starting from 0 and continuing with 1, 2, 3, up to  $2^k - 1$  where k is the number of address lines. The selection of a specific word inside the memory is done by applying the k-bit binary address to the address lines. A decoder inside the memory accepts this address and opens the paths needed to select the bits of the specified word. Computer memories may range from 1024 words, requiring an address of 10 bits, to  $2^{32}$  words, requiring 32 address bits. It is customary to refer to the number of words (or bytes) in a memory with one of the letters K (kilo), M (mega), or G (giga). K is equal to  $2^{10}$ , M is equal to  $2^{20}$ , and G is equal to  $2^{30}$ . Thus,  $64K = 2^{16}$ ,  $2M = 2^{21}$ , and  $4G = 2^{32}$ .

Two major types of memories are used in computer systems: random-access memory (RAM) and read-only memory (ROM). These semiconductor memories are classified into Random Access Memories (RAMs) and Sequential Access Memories (SAMs) based on access time. Memories constructed with shift registers, Charge Coupled Devices (CCDs), or bubble memories are examples of SAMs. RAMs are categorized into ROMs, Read Mostly Memories (RMMs), and Read Write Memories (RWMs). ROMs are of two types: Masked Programmed

ROMs and user Programmed PROMs. Two types of RMMs are Erasable and Programmable (EPROM), and Electrically Erasable (EEPROM). RWMs are Static RAM (SRAM) and Dynamic RAM (DRAM). Static RAMs have memory cells as common Flip-Flops. Dynamic RAMs have memory cells that must be refreshed, read and written periodically to avoid loss of memory cells.

### Random-Access Memory

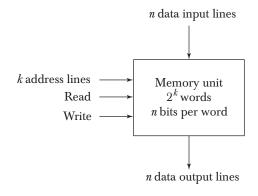
In random-access memory (RAM) the memory cells can be accessed for information transfer from any desired random location. That is, the process of locating a word in memory is the same and requires an equal amount of time no matter where the cells are located physically in memory: thus the name "random access."

Communication between a memory and its environment is achieved through data input and output lines, address selection lines, and control lines that specify the direction of transfer. A block diagram of a RAM unit is shown in Fig. 2-13. The n data input lines provide the information to be stored in memory, and the n data output lines supply the information coming out of memory. The k address lines provide a binary number of k bits that specify a particular word chosen among the  $2^k$  available inside the memory. The two control inputs specify the direction of transfer desired.

The two operations that a random-access memory can perform are the write and read operations. The write signal specifies a transfer-in operation and the read signal specifies a transfer-out operation. On accepting one of these control signals, the internal circuits inside the memory provide the desired function. The steps that must be taken for the purpose of transferring a new word to be stored into memory are as follows:

- 1. Apply the binary address of the desired word into the address lines.
- 2. Apply the data bits that must be stored in memory into the data input lines.
- **3.** Activate the *write* input.

Figure 2-13 Block diagram of random access memory (RAM).



RAM

write and read operations

The memory unit will then take the bits presently available in the input data lines and store them in the word specified by the address lines.

The steps that must be taken for the purpose of transferring a stored word out of memory are as follows:

- **1.** Apply the binary address of the desired word into the address lines.
- 2. Activate the *read* input.

The memory unit will then take the bits from the word that has been selected by the address and apply them into the output data lines. The content of the selected word does not change after reading.

## Read-Only Memory

As the name implies, a read-only memory (ROM) is a memory unit that performs the read operation only; it does not have a write capability. This implies that the binary information stored in a ROM is made permanent during the hardware production of the unit and cannot be altered by writing different words into it. Whereas a RAM is a general-purpose device whose contents can be altered during the computational process, a ROM is restricted to reading words that are permanently stored within the unit. The binary information to be stored, specified by the designer, is then embedded in the unit to form the required interconnection pattern. ROMs come with special internal electronic fuses that can be "programmed" for a specific configuration. Once the pattern is established, it stays within the unit even when power is turned off and on again.

An  $m \times n$  ROM is an array of binary cells organized into m words of n bits each. As shown in the block diagram of Fig. 2-14, a ROM has k address input lines to select one of  $2^k = m$  words of memory, and n output lines, one for each bit of the word. An integrated circuit ROM may also have one or more enable inputs for expanding a number of packages into a ROM with larger capacity.

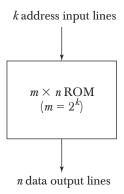


Figure 2-14 Block diagram of read only memory (ROM).

The ROM does not need a read-control line since at any given time, the output lines automatically provide the *n* bits of the word selected by the address value. Because the outputs are a function of only the present inputs (the address lines), a ROM is classified as a combinational circuit. In fact, a ROM is constructed internally with decoders and a set of OR gates. There is no need for providing storage capabilities as in a RAM, since the values of the bits in the ROM are permanently fixed.

ROMs find a wide range of applications in the design of digital systems. Basically, a ROM generates an input–output relation specified by a truth table. As such, it can implement any combinational circuit with k inputs and n outputs. When employed in a computer system as a memory unit, the ROM is used for storing fixed programs that are not to be altered and for tables of constants that are not subject to change. ROM is also employed in the design of control units for digital computers. As such, they are used to store coded information that represents the sequence of internal control variables needed for enabling the various operations in the computer. A control unit that utilizes a ROM to store binary control information is called a microprogrammed control unit. This subject is dicsussed in more detail in Chapter 7.

# Types of ROMs

The required paths in a ROM may be programmed in three different ways. The first, *mask programming*, is done by the semiconductor company during the last fabrication process of the unit. The procedure for fabricating a ROM requires that the customer fill out the truth table that he or she wishes the ROM to satisfy. The truth table may be submitted in a special form provided by the manufacturer or in a specified format on a computer output medium. The manufacturer makes the corresponding mask for the paths to produce the l's and 0's according to the customer's truth table. This procedure is costly because the vendor charges the customer a special fee for custom masking the particular ROM. For this reason, mask programming is economical only if a large quantity of the same ROM configuration is to be ordered.

For small quantities it is more economical to use a second type of ROM called a *programmable read-only memory* or PROM. When ordered, PROM units contain all the fuses intact, giving all l's in the bits of the stored words. The fuses in the PROM are blown by application of current pulses through the output terminals for each address. A blown fuse defines a binary 0 state, and an intact fuse gives a binary 1 state. This allows users to program PROMs in their own laboratories to achieve the desired relationship between input addresses and stored words. Special instruments called *PROM programmers* are available commercially to facilitate this procedure. In any case, all procedures for programming ROMs are hardware procedures even though the word "programming" is used.

The hardware procedure for programming ROMs or PROMs is irreversible, and once programmed, the fixed pattern is permanent and cannot be altered. Once a bit pattern has been established, the unit must be discarded if the bit pattern is to be changed. A third type of ROM available is called *erasable PROM* or EPROM.

**PROM** 

The EPROM can be restructured to the initial value even though its fuses have been blown previously. When the EPROM is placed under a special ultraviolet light for a given period of time, the shortwave radiation discharges the internal gates that serve as fuses. After erasure, the EPROM returns to its initial state and can be reprogrammed to a new set of words. Certain PROMs can be erased with electrical signals instead of ultraviolet light. These PROMs are called *electrically erasable PROM* or EEPROM. Flash memory is a form of EEPROM in which a block of bytes can be erased in a very short duration. Example applications of EEPROM devices are:

**EEPROM** 

- 1. storing current time and date in a machine.
- 2. storing port statusses.

Examples of flash memory device applications are:

- 1. storing messages in a mobile phone.
- 2. storing photographs in a digital camera.

#### **PROBLEMS**

- 2-1. TTL SSI come mostly in 14-pin 1C packages. Two pins are reserved for power supply and the other pins are used for input and output terminals. How many circuits are included in one such package if it contains the following type of circuits? (a) Inverters; (b) two-input exclusive-OR gates; (c) three-input OR gates; (d) four-input AND gates; (e) five-input NOR gates; (f) eight-input NAND gates; (g) clocked *JK* flip-flops with asynchronous clear.
- 2-2. MSI chips perform elementary digital functions such as decoders, multiplexers, registers, and counters. The following are TTL-type integrated circuits that provide such functions. Find their description in a data book and compare them with the corresponding component presented in this chapter.
  - **a.** IC type 74155 dual 2-to-4-line decoders.
  - **b.** IC type 74157 quadruple 2-to-l-line multiplexers.
  - **c.** IC type 74194 4-bit bidirectional shift register with parallel load.
  - d. IC type 74163 4-bit binary counter with parallel load and synchronous clear.
- **2-3.** Construct a 5-to-32-line decoder with four 3-to-8-line decoders with enable and one 2-to-4-line decoder. Use block diagrams similar to Fig. 2-4.
- **2-4.** Draw the logic diagram of a 2-to-4-line decoder with only NOR gates. Include an enable input.
- **2-5.** Modify the decoder of Fig. 2-3 so that the circuit is enabled when E = 1 and disabled when E = 0. List the modified truth table.
- **2-6.** Draw the logic diagram of an eight-input, three-output encoder whose truth table is given in Table 2-2. What is the output when all the inputs are equal to 0? What is the output when only input  $D_0$  is equal to 0? Establish a procedure that will distinguish between these two cases.

- 2-7. Construct a 16-to-l-line multiplexer with two 8-to-l-line multiplexers and one 2-to-l-line multiplexer. Use block diagrams for the three multiplexers.
- **2-8.** Draw the block diagram of a dual 4-to-l-line multiplexers and explain its operation by means of a function table.
- 2-9. Include a two-input AND gate with the register of Fig. 2-7 and connect the gate output to the clock inputs of all the flip-flops. One input of the AND gate receives the clock pulses from the clock pulse generator. The other input of the AND gate provides a parallel load control. Explain the operation of the modified register.
- **2-10.** What is the purpose of the buffer gate in the clock input of the register of Fig. 2-8?
- 2-11. Include a synchronous clear capability to the register with parallel load of Fig. 2-8.
- 2-12. The content of a 4-bit register is initially 1101. The register is shifted six times to the right with the serial input being 101101. What is the content of the register after each shift?
- **2-13.** What is the difference between serial and parallel transfer? Using a shift register with parallel load, explain how to convert serial input data to parallel output and parallel input data to serial output.
- **2-14.** A ring counter is a shift register as in Fig. 2-9 with the serial output connected to the serial input. Starting from an initial state of 1000, list the sequence of states of the four flip-flops after each shift.
- **2-15.** The 4-bit bidirectional shift register with parallel load shown in Fig. 2-10 is enclosed within one IC package.
  - a. Draw a block diagram of the IC showing all inputs and outputs. Include two pins for power supply.
  - b. Draw a block diagram using two ICs to produce an 8-bit bidirectional shift register with parallel load.
- 2-16. How many flip-flops will be complemented in a 10-bit binary counter to reach the next count after (a) 1001100111; (b) 0011111111?
- 2-17. Show the connections between four 4-bit binary counters with parallel load (Fig. 2-12) to produce a 16-bit binary counter with parallel load. Use a block diagram for each 4-bit counter.
- **2-18.** Show how the binary counter with parallel load of Fig. 2-12 can be made to operate as a divide-by-*N* counter (i.e., a counter that counts from 0000 to *N*-and back to 0000). Specifically show the circuit for a divide-by-10 counter using the counter of Fig. 2-12 and an external AND gate.
- 2-19. The following memory units are specified by the number of words times the number of bits per word. How many address lines and input-output data lines are needed in each case? (a)  $2K \times 16$ ; (b)  $64K \times 8$ ; (c)  $16M \times 32$ ; (d)  $4G \times 64$ .
- **2-20.** Specify the number of bytes that can be stored in the memories listed in Prob. 2–19.
- **2-21.** How many  $128 \times 8$  memory chips are needed to provide a memory capacity of  $4096 \times 16$ ?
- **2-22.** Given a  $32 \times 8$  ROM chip with an enable input, show the external connections necessary to construct a  $128 \times 8$  ROM with four chips and a decoder.
- 2-23. A ROM chip of 4096 × 8 bits has two enable inputs and operates from a 5-volt power supply. How many pins are needed for the integrated circuit package? Draw a block diagram and label all input and output terminals in the ROM.

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